imall

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832 Email & Skype: info@chipsmall.com Web: www.chipsmall.com Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China



Triacs Silicon Bidirectional Thyristors

Designed primarily for full-wave ac control applications, such as motor controls, heating controls or dimmers; or wherever full-wave, silicon gate-controlled devices are needed.

Features

- Uniform Gate Trigger Currents in Three Quadrants, Q1, Q2, and Q3
- High Commutating di/dt and High Immunity to dv/dt @ 125°C
- Minimizes Snubber Networks for Protection
- Blocking Voltage to 800 Volts
- On-State Current Rating of 12 Amperes RMS at 80°C
- High Surge Current Capability 100 Amperes
- Industry Standard TO-220AB Package for Ease of Design
- Glass Passivated Junctions for Reliability and Uniformity
- These Devices are Pb-Free and are RoHS Compliant*

MAXIMUM RATINGS (T_{.1} = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Peak Repetitive Off-State Voltage (Note 1) ($T_J = -40$ to 125°C, Sine Wave, 50 to 60 Hz, Gate Open)	V _{DRM,} V _{RRM}		V
MAC12HCDG MAC12HCMG MAC12HCNG		400 600 800	
On-State RMS Current (All Conduction Angles; $T_C = 80^{\circ}C$)	I _{T(RMS)}	12	A
Peak Non-Repetitive Surge Current (One Full Cycle, 60 Hz, $T_J = 125^{\circ}C$)	I _{TSM}	100	A
Circuit Fusing Consideration (t = 8.33 ms)	l ² t	41	A ² sec
Peak Gate Power (Pulse Width \leq 1.0 μ s, T _C = 80°C)	P _{GM}	16	W
Average Gate Power (t = 8.3 ms, $T_C = 80^{\circ}C$)	$P_{G(AV)}$	0.35	W
Operating Junction Temperature Range	TJ	-40 to +125	°C
Storage Temperature Range	T _{stg}	-40 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

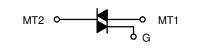
V_{DRM} and V_{RRM} for all types can be applied on a continuous basis. Blocking 1. voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

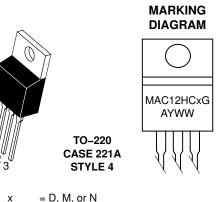


ON Semiconductor®

www.onsemi.com







= Assembly Location (Optional)* А

= Year

Υ ww = Work Week

= Pb-Free Package G

* The Assembly Location code (A) is optional. In cases where the Assembly Location is stamped on the package the assembly code may be blank.

	PIN ASSIGNMENT
1	Main Terminal 1
2	Main Terminal 2
3	Gate
4	Main Terminal 2

ORDERING INFORMATION

Device	Package	Shipping
MAC12HCDG	TO–220 (Pb–Free)	50 Units / Rail
MAC12HCMG	TO–220 (Pb–Free)	50 Units / Rail
MAC12HCNG	TO-220 (Pb-Free)	50 Units / Rail

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

MAC12HC/D

THERMAL CHARACTERISTICS

Characteristic	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case Junction-to-Ambient	$R_{ heta JC} \ R_{ heta JA}$	2.2 62.5	°C/W
Maximum Lead Temperature for Soldering Purposes 1/8" from Case for 10 Seconds	ΤL	260	°C

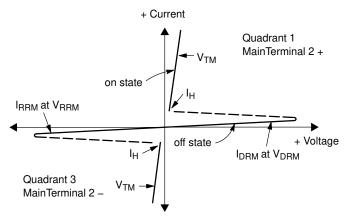
ELECTRICAL CHARACTERISTICS ($T_J = 25^{\circ}C$ unless otherwise noted; Electricals apply in both directions)

Characteristic		Symbol	Min	Тур	Max	Unit
DFF CHARACTERISTICS						
Peak Repetitive Blocking Current (V_D = Rated V_{DRM} , V_{RRM} , Gate Open)	T _J = 25°C T _J = 125°C	I _{DRM} , I _{RRM}		-	0.01 2.0	mA
ON CHARACTERISTICS						
Peak On-State Voltage (Note 2) $(I_{TM} = \pm 17 \text{ A})$		V _{TM}	_	_	1.85	V
Gate Trigger Current (Continuous dc) (V _D = 12 V, R _L = 100 Ω) MT2(+), G(+) MT2(+), G(-) MT2(-), G(-)		I _{GT}	10 10 10		50 50 50	mA
Holding Current ($V_D = 12 V$, Gate Open, Initiating Current = ±150 mA)		Ι _Η	_	_	60	mA
Latch Current (V _D = 12 V, I _G = 50 mA) MT2(+), G(+) MT2(+), G(-) MT2(-), G(-)		ι	- - -		60 80 60	mA
Gate Trigger Voltage (Continuous dc) ($V_D = 12 V$, $R_L = 100 \Omega$) MT2(+), G(+) MT2(+), G(-) MT2(-), G(-)		V _{GT}	0.5 0.5 0.5		1.5 1.5 1.5	V
DYNAMIC CHARACTERISTICS						
Rate of Change of Commutating Current ($V_D = 400 \text{ V}, I_{TM} = 4.4 \text{ A}, \text{ Commutating dv/dt} = 18 \text{ V/}\mu\text{s}, \text{ Gate Open}$ $T_J = 125^{\circ}\text{C}, f = 250 \text{ Hz}, C_L = 10 \ \mu\text{F}, L_L = 40 \text{ mH}, \text{ with Snubber}$)	,	(di/dt) _c	15	-	-	A/ms
Critical Rate of Rise of Off-State Voltage $(V_D = Rated V_{DRM}, Exponential Waveform, Gate Open, T_J = 125°C)$		dv/dt	600	-	-	V/µs
Repetitive Critical Rate of Rise of On-State Current IPK = 50 A; PW = 40 μ sec; diG/dt = 200 mA/ μ sec; f = 60 Hz		di/dt	-	-	10	A/μs

J Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions. 2. Pulse Test: Pulse Width \leq 2.0 ms, Duty Cycle \leq 2%.

Voltage Current Characteristic of Triacs (Bidirectional Device)

Symbol	Parameter
V _{DRM}	Peak Repetitive Forward Off State Voltage
I _{DRM}	Peak Forward Blocking Current
V _{RRM}	Peak Repetitive Reverse Off State Voltage
I _{RRM}	Peak Reverse Blocking Current
V _{TM}	Maximum On State Voltage
Ι _Η	Holding Current

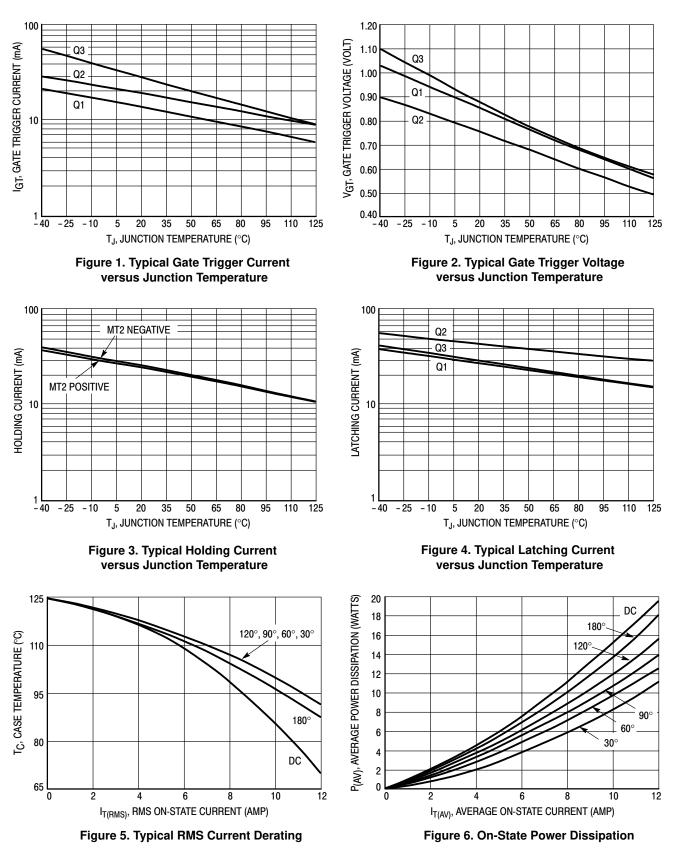


MT2 POSITIVE (Positive Half Cycle) (+) MT2 (+) MT2 Quadrant II Quadrant I (-) I_{GT} GATE (+) I_{GT} GATE 0 o **ф** МТ1 **ф** МТ1 -REF REF I_{GT} + I_{GT} (-) MT2 (-) MT2 Quadrant III **Quadrant IV** (+) I_{GT} GATE (-) I_{GT} 0 0 **ф** МТ1 MT1 Ξ Ξ REF REF MT2 NEGATIVE (Negative Half Cycle)

Quadrant Definitions for a Triac

All polarities are referenced to MT1.

With in-phase signals (using standard AC lines) quadrants I and III are used.



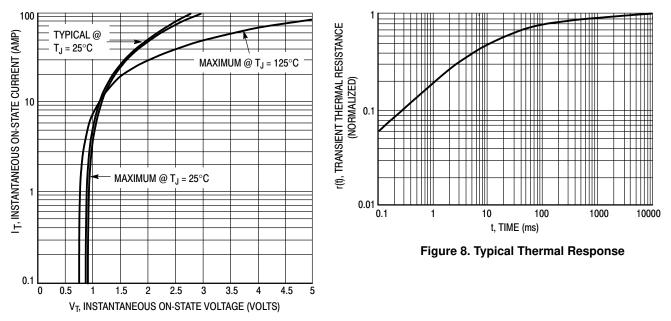
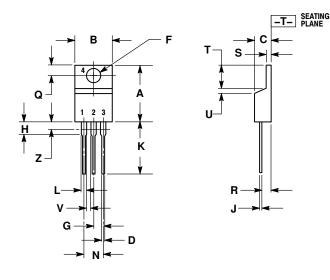


Figure 7. Typical On-State Characteristics

PACKAGE DIMENSIONS

TO-220 CASE 221A-09 **ISSUE AH**



NOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. CONTROLLING DIMENSION: INCH.

2.

3 DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.570	0.620	14.48	15.75
В	0.380	0.415	9.66	10.53
С	0.160	0.190	4.07	4.83
D	0.025	0.038	0.64	0.96
F	0.142	0.161	3.61	4.09
G	0.095	0.105	2.42	2.66
н	0.110	0.161	2.80	4.10
J	0.014	0.024	0.36	0.61
Κ	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
Ν	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
Т	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
۷	0.045		1.15	
Z		0.080		2.04

STYLE 4: PIN 1. MAIN TERMINAL 1 MAIN TERMINAL 2 2. 3. GATE MAIN TERMINAL 2 Λ

ON Semiconductor and the 💷 are registered trademarks of Semiconductor Components Industries, LLC (SCILLC) or its subsidiaries in the United States and/or other countries. SCILLC owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other industries, LEC (SOLLC) of its substances interval or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor P.O. Box 5163, Denver, Colorado 80217 USA Phone: 303–675–2175 or 800–344–3860 Toll Free USA/Canada Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com

N. American Technical Support: 800-282-9855 Toll Free USA/Canada Europe, Middle East and Africa Technical Support:

Phone: 421 33 790 2910 Japan Customer Focus Center Phone: 81-3-5817-1050

ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative